

Supplementary Material

Pattern Pick and Place Method for Twisted Bi- and Multi-Layer Graphene

Jae-Young Lim ^{1,§}, Hyeon-Sik Jang ^{1,§}, Hyun-Jae Yoo ¹, Seung-il Kim ² and Dongmok Whang ^{1,*}

¹ SKKU Advanced Institute of Nanotechnology (SAINT) and School of Advanced Materials Science and Engineering Sungkyunkwan University (SSKU), 2066, Seobu-Ro, Jangan-Gu, Suwon-Si, Gyeonggi-Do 16419, Korea; limjyyy@skku.edu (J.-Y.L.); dagu1821@skku.edu (H.-S.J.); silverains2@gmail.com (H.-J.Y.)

² Department of Energy Systems Research and Department of Materials Science and Engineering Ajou University, 2016, World cup-Ro, Yeongtong-Gu, Suwon-Si, Gyeonggi-Do 16499, Korea; stmdldfs@gmail.com

* Correspondence: dwhang@skku.edu; Tel.: +82-31-290-7399

§ These authors contributed equally to this work.

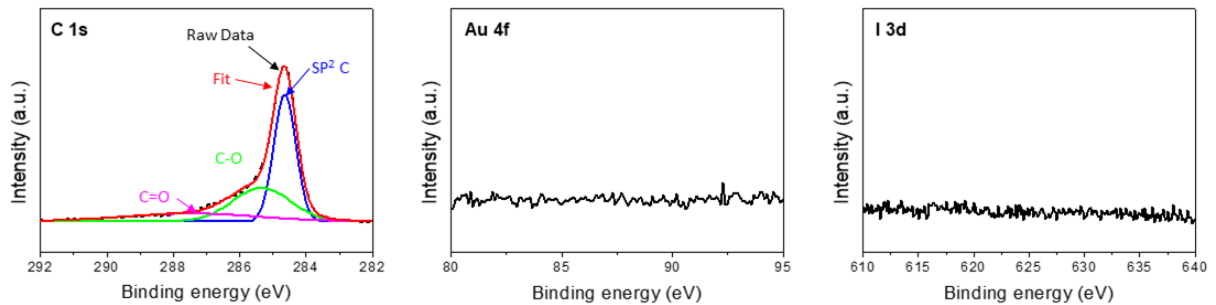


Figure S1. The XPSs results of tBLG at each C 1s, Au 4f, and I 3d.

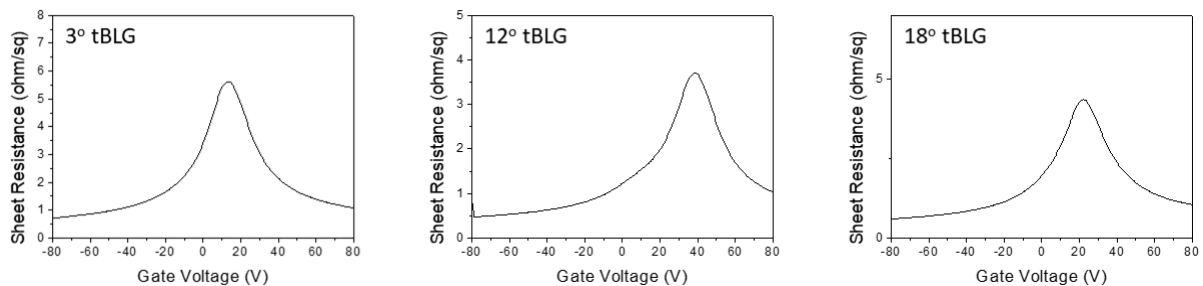


Figure S2. Back gate dependent sheet resistance graphs for 3°, 12°, and 18° tBLG devices.